

## N-Channel Super Junction Power MOSFET IV

### General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

### Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

$V_{DS\ min@T_{jmax}}$	710	V
$R_{DS(ON)TYP}$	165	mΩ
$I_D$	18	A
$Q_g$	30	nC



Schematic diagram

✧ Intrinsic fast-recovery body diode

### Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF190T	TO-247	NCE65NF190T

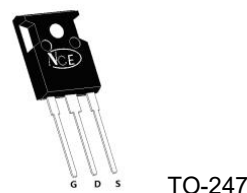


Table 1. Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS}=0V$ )	$V_{DS}$	650	V
Gate-Source Voltage ( $V_{DS}=0V$ ) AC ( $f>1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	V
Gate-Source Voltage ( $V_{DS}=0V$ ) DC	$V_{GS}$	$\pm 20$	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	18	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	12.6	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	54	A
Maximum Power Dissipation( $T_c=25^\circ\text{C}$ )	$P_D$	194	W
Derate above $25^\circ\text{C}$		1.29	W/ $^\circ\text{C}$
Avalanche current(Note 1)	$I_{AS}$	4	A
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$ ,	$dv/dt$	50	V/ns
Reverse diode $dv/dt$ , $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	$dv/dt$	50	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	$-55...+175$	$^\circ\text{C}$

\* limited by maximum junction temperature

**Table 2. Thermal Characteristic**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	$R_{thJC}$	0.77	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	$R_{thJA}$	62	$^{\circ}\text{C}/\text{W}$

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			300	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =9A		165	190	mΩ
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz		1550	1950	pF
Output Capacitance	C <sub>oss</sub>			60		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			5		pF
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =480V, I <sub>D</sub> =9A, V <sub>GS</sub> =10V		30		nC
Gate-Source Charge	Q <sub>gs</sub>			12.5		nC
Gate-Drain Charge	Q <sub>gd</sub>			11		nC
Gate plateau voltage	V <sub>gp</sub>			7.5		V
Intrinsic gate resistance	R <sub>G</sub>	f = 1 MHz open drain		1.5		Ω
Switching times						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =380V, I <sub>D</sub> =9A, R <sub>G</sub> =1.7Ω, V <sub>GS</sub> =10V		43		nS
Turn-on Rise Time	t <sub>r</sub>			17		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			94		nS
Turn-Off Fall Time	t <sub>f</sub>			26		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I <sub>SD</sub>	T <sub>C</sub> =25℃			18	A
Pulsed Source-drain current(Body Diode)	I <sub>SDM</sub>				54	A
Forward On Voltage	V <sub>SD</sub>	T <sub>J</sub> =25℃, I <sub>SD</sub> =18A, V <sub>GS</sub> =0V		0.9	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> =25℃, I <sub>F</sub> =9A, di/dt=100A/μs		125		nS
Reverse Recovery Charge	Q <sub>rr</sub>			0.51		uC
Peak Reverse Recovery Current	I <sub>rrm</sub>			8.2		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

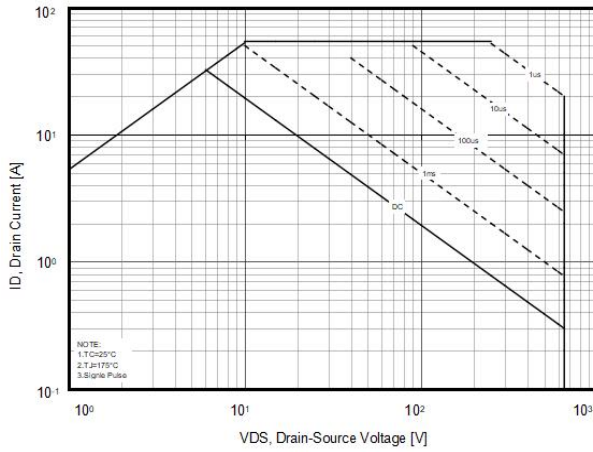


Figure2. Capacitance

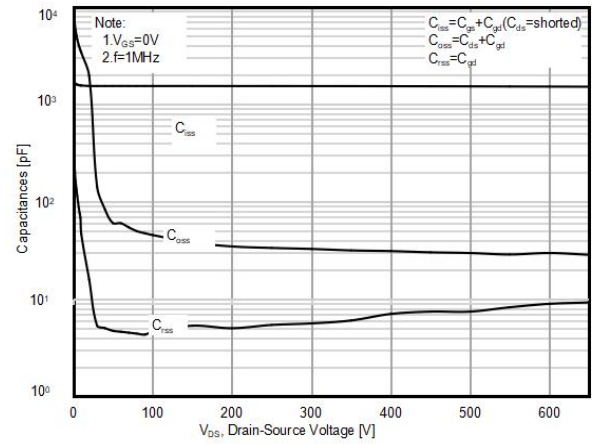


Figure3. Transfer characteristics

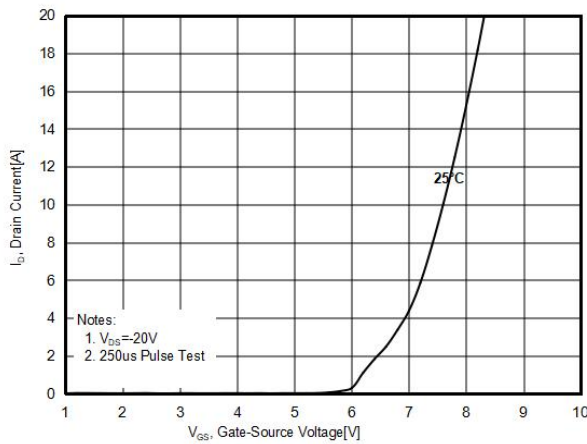


Figure4. Output characteristics

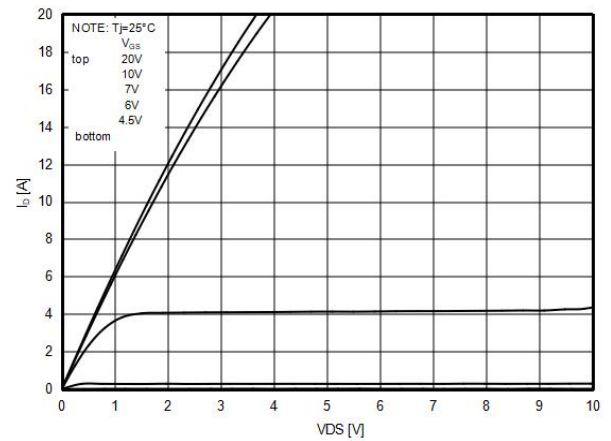


Figure5.  $R_{DS(ON)}$  vs Junction Temperature

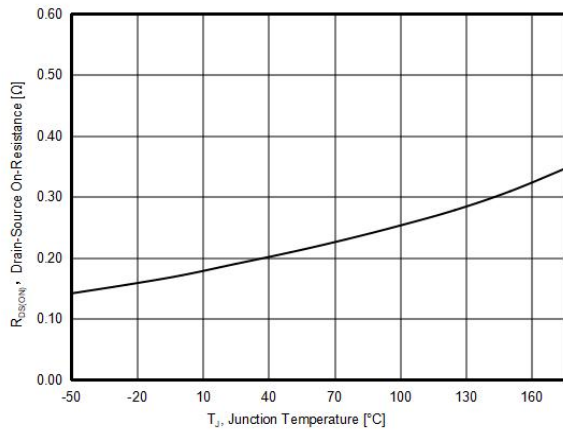
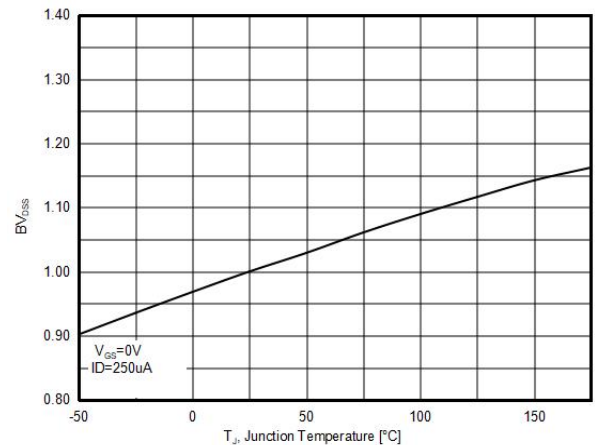
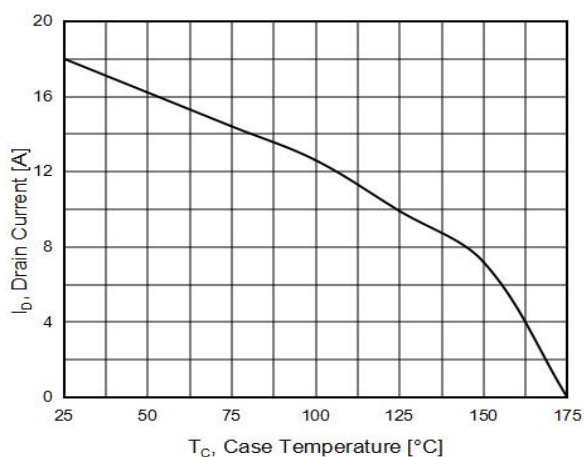


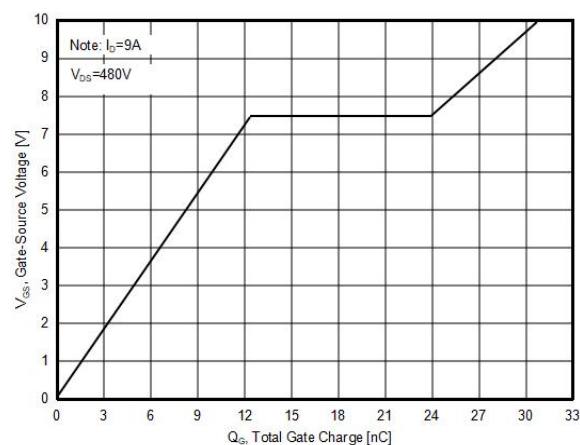
Figure6.  $BV_{DSS}$  vs Junction Temperature



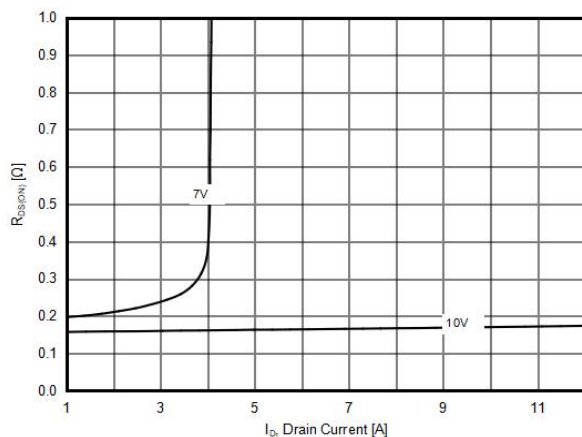
**Figure7. Maximum  $I_D$  vs Junction Temperature**



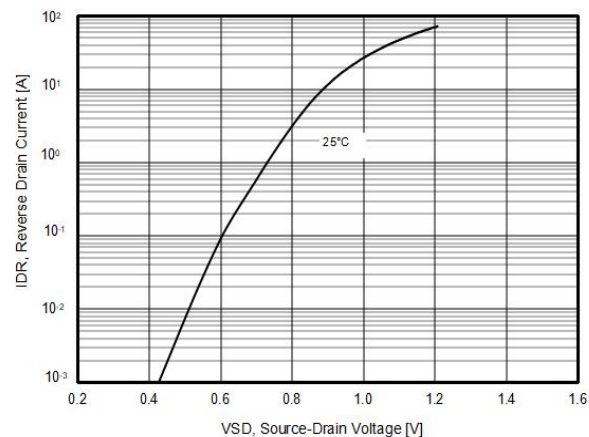
**Figure8. Gate charge waveforms**



**Figure9. Static drain-source on resistance**



**Figure10. Source-Drain Diode Forward Voltage**



## Test circuit

### 1) Gate charge test circuit & Waveform



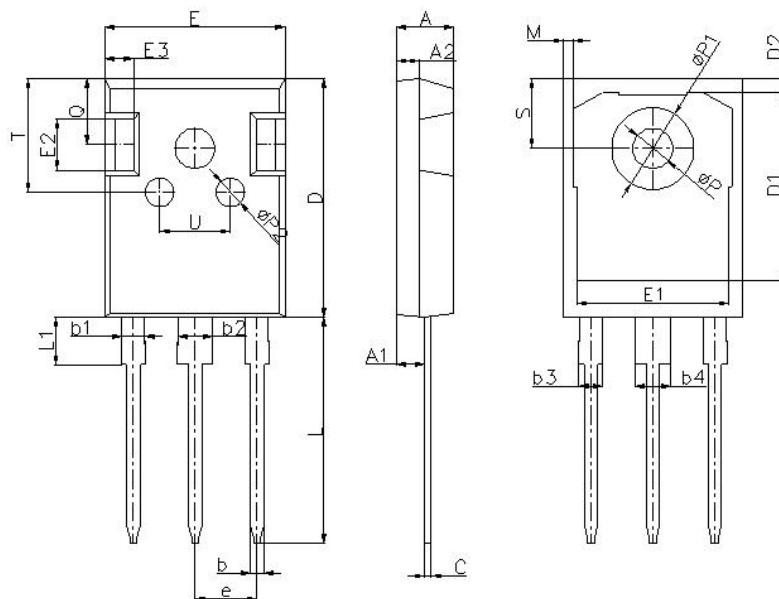
### 2) Switch Time Test Circuit:



### 3) Unclamped Inductive Switching Test Circuit & Waveforms



## TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.077	0.081
b2	2.96	3.06	0.117	0.120
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
E2	4.40	4.60	0.173	0.181
E3	2.40	2.60	0.094	0.102
e	5.436BSC		0.214BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
M	0.35	0.95	0.014	0.037
P	3.40	3.60	0.134	0.142
P1	7.00	7.40	0.276	0.291
P2	2.40	2.60	0.094	0.102
Q	5.60	6.00	0.220	0.236
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402
U	6.00	6.40	0.236	0.252

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